

BAS16WS

PRV : 100 Volts
Io : 250 mA

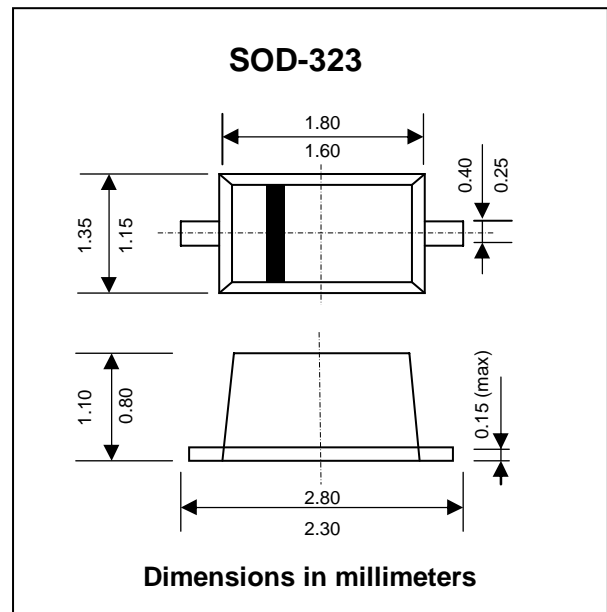
FEATURES :

- * Silicon Epitaxial Planar Diode
- * Fast switching diodes.
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : SOD-323 plastic Case
- * Weight : approx. 0.004 g

SMALL SIGNAL DIODE



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Rectified Current (Continuous)	$I_{F(AV)}$	250	mA
Surge Forward Current at $t = 1$ s and $T_j = 25$ °C	I_{FSM}	500	mA
Power Dissipation at $T_{amb} = 25$ °C	P_{tot}	200 ¹⁾	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	-65 to + 150	°C

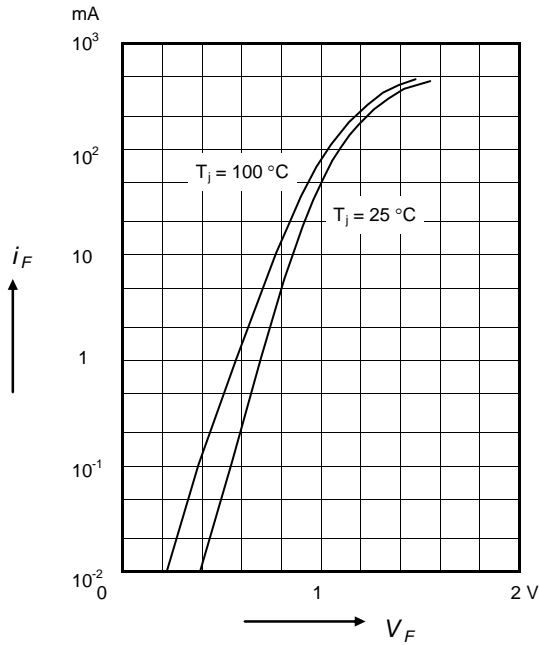
ELECTRICAL CHARACTERISTICS (Rating at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 50$ mA	V_F	-	-	1	V
Leakage Current	at $V_R=25$ V, $T_j=150$ °C	I_R	-	30	nA
	at $V_R = 75$ V	I_R	-	1	μA
	at $V_R=75$ V, $T_j=150$ °C	I_R	-	50	μA
Capacitance at $V_F = V_R = 0$ V	C_{tot}	-	-	4	pF
Reverse Recovery Time from $I_F = 10$ mA to $I_R = 10$ mA, $I_R = 6$ V, $R_L = 100$ Ω	T_{rr}	-	-	6	ns
Thermal Resistance Junction to Ambient Air	R_{thJA}	-	-	650 ¹⁾	°C/W

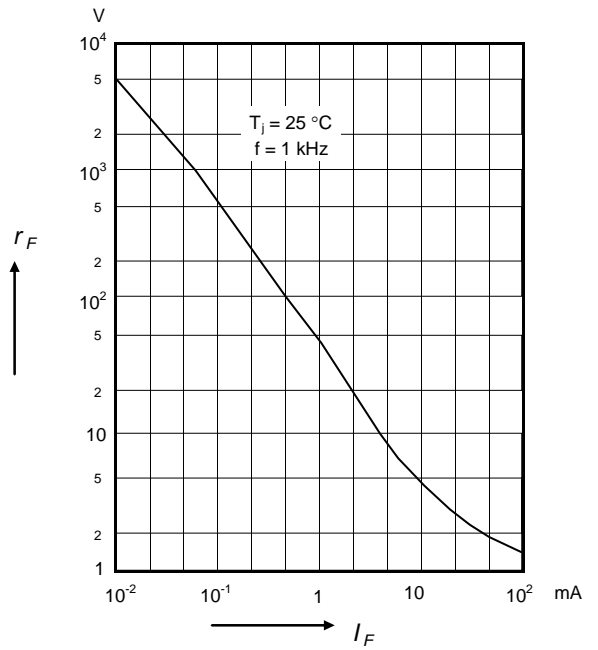
Note : 1) Valid provided that electrodes are kept at ambient temperature

RATINGS AND CHARACTERISTIC CURVES (BAS16WS)

Forward characteristics

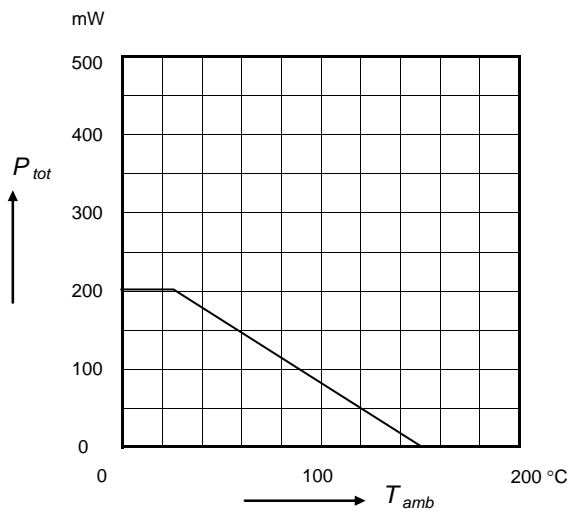


Dynamic forward resistance versus forward current



Admissible power dissipation versus ambient temperature

For conditions, see footnote in table "Absolute Maximum Ratings"



Relative capacitance versus reverse voltage

